

P-Channel 30-V (D-S) MOSFET

PRODUCT SUMMARY

V_{DS} (V)	$R_{DS(on)}$ (Ω)	I_D (A) ^d	Q_g (Typ.)
- 30	0.005 at $V_{GS} = - 10$ V	- 29	61 nC
	0.00775 at $V_{GS} = - 4.5$ V	- 23	

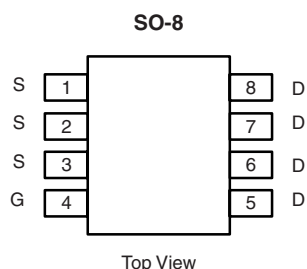
FEATURES

- Halogen-free
- TrenchFET® Power MOSFET
- 100 % R_g Tested
- 100 % UIS Tested

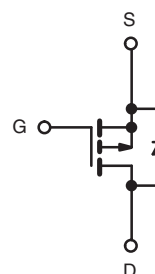

RoHS
COMPLIANT

APPLICATIONS

- Adaptor Switch
- Notebook



Ordering Information: Si4459ADY-T1-GE3 (Lead (Pb)-free and Halogen-free)



P-Channel MOSFET

ABSOLUTE MAXIMUM RATINGS $T_A = 25$ °C, unless otherwise noted

Parameter	Symbol	Limit	Unit
Drain-Source Voltage	V_{DS}	- 30	V
Gate-Source Voltage	V_{GS}	± 20	
Continuous Drain Current ($T_J = 150$ °C)	I_D	$T_C = 25$ °C	- 29
		$T_C = 70$ °C	- 23.5
		$T_A = 25$ °C	- 19.7 ^{a, b}
		$T_A = 70$ °C	- 15.6 ^{a, b}
Pulsed Drain Current	I_{DM}	- 70	A
Continuous Source-Drain Diode Current	I_S	$T_C = 25$ °C	- 6.5
		$T_A = 25$ °C	- 2.9 ^{a, b}
Avalanche Current	I_{AS}	- 30	
Single-Pulse Avalanche Energy	E_{AS}	45	mJ
Maximum Power Dissipation	P_D	$T_C = 25$ °C	7.8
		$T_C = 70$ °C	5.0
		$T_A = 25$ °C	3.5 ^{a, b}
		$T_A = 70$ °C	2.2 ^{a, b}
Operating Junction and Storage Temperature Range	T_J, T_{stg}	- 55 to 150	°C

THERMAL RESISTANCE RATINGS

Parameter	Symbol	Typical	Maximum	Unit
Maximum Junction-to-Ambient ^{a, c}	R_{thJA}	29	35	°C/W
Maximum Junction-to-Foot	R_{thJF}	13	16	

Notes:

a. Surface mounted on 1" x 1" FR4 board.

b. $t = 10$ s.

c. Maximum under Steady State conditions is 80 °C/W.

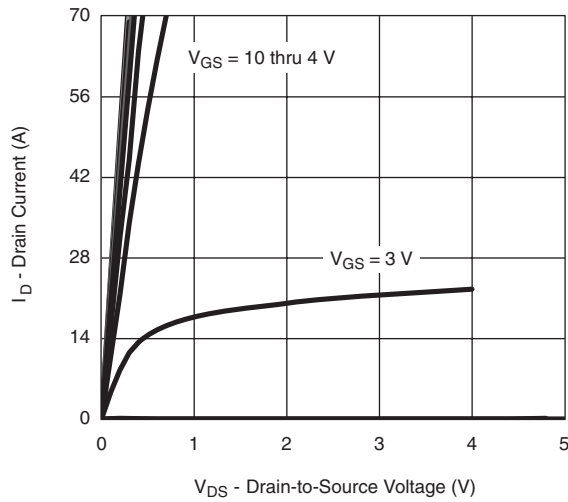
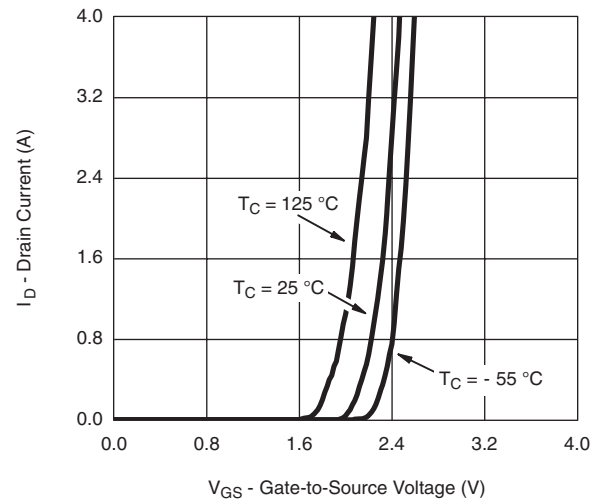
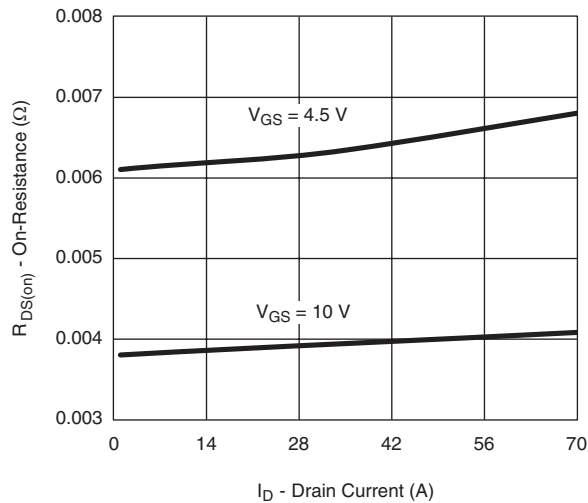
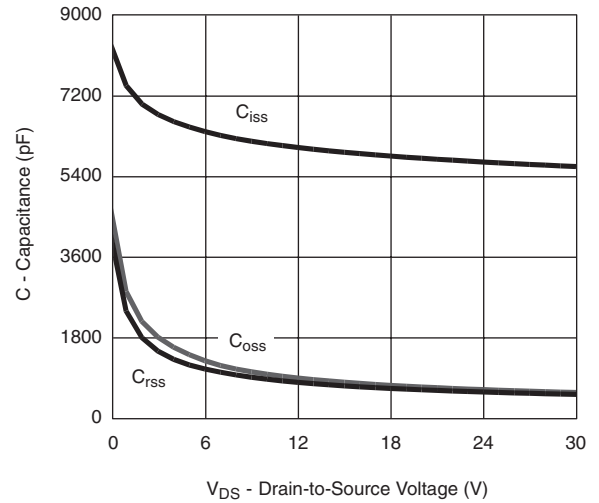
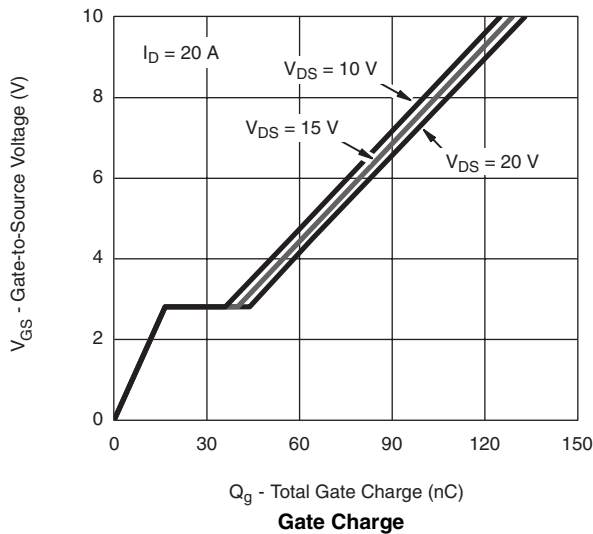
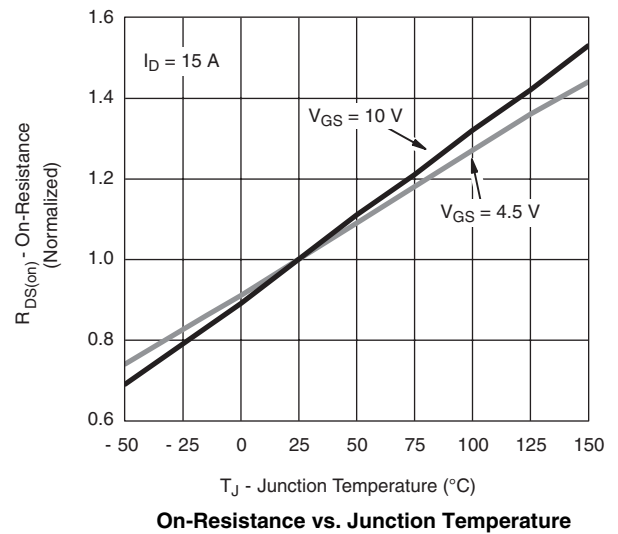
d. Based on $T_C = 25$ °C.

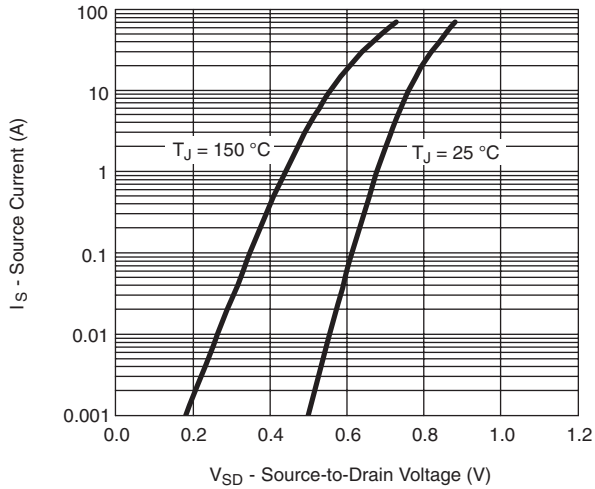
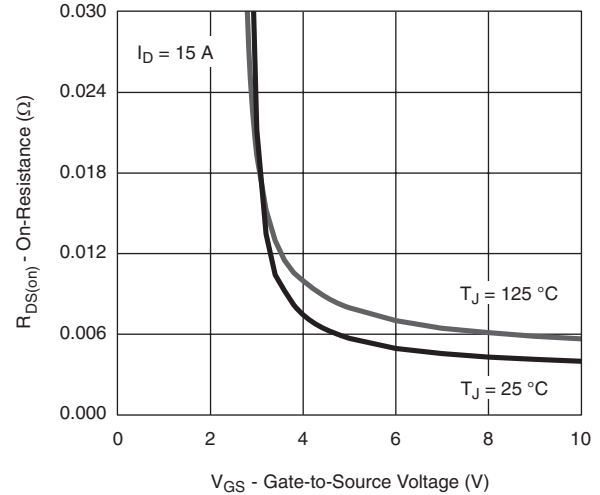
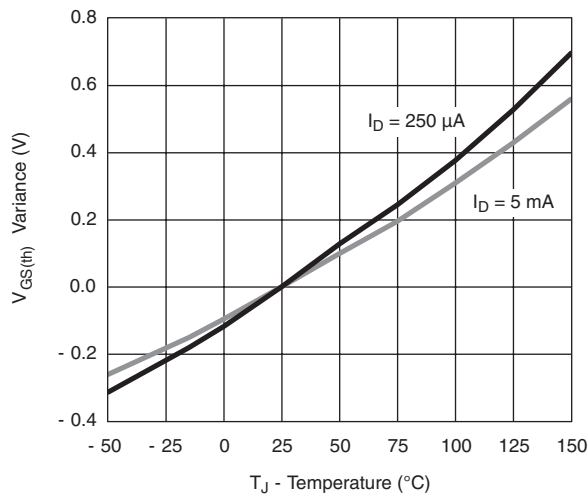
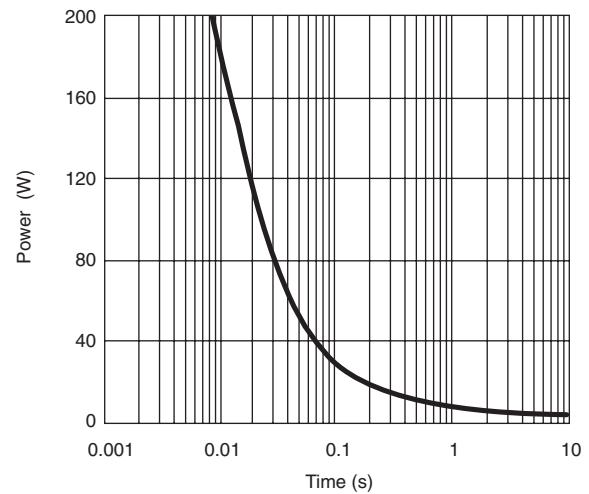
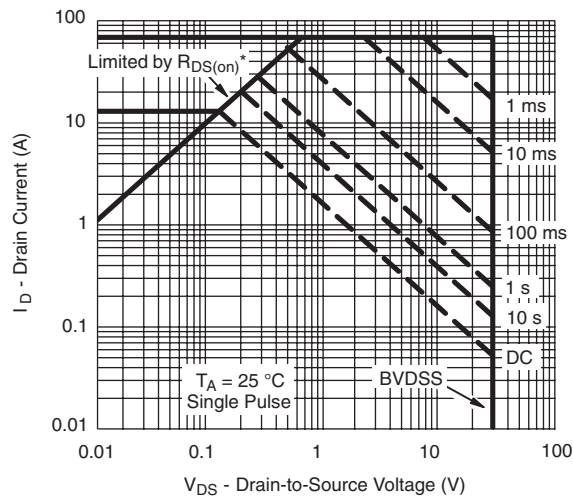
SPECIFICATIONS T _J = 25 °C, unless otherwise noted						
Parameter	Symbol	Test Conditions	Min.	Typ.	Max.	Unit
Static						
Drain-Source Breakdown Voltage	V _{DS}	V _{GS} = 0 V, I _D = - 250 μA	- 30			V
V _{DS} Temperature Coefficient	ΔV _{DS} /T _J	I _D = - 250 μA		- 31		mV/°C
V _{GS(th)} Temperature Coefficient	ΔV _{GS(th)} /T _J			5.3		
Gate-Source Threshold Voltage	V _{GS(th)}	V _{DS} = V _{GS} , I _D = - 250 μA	- 1.0		- 2.5	V
Gate-Source Leakage	I _{GSS}	V _{DS} = 0 V, V _{GS} = ± 20 V			± 100	nA
Zero Gate Voltage Drain Current	I _{DSS}	V _{DS} = - 30 V, V _{GS} = 0 V			- 1	μA
		V _{DS} = - 30 V, V _{GS} = 0 V, T _J = 55 °C			- 5	
On-State Drain Current ^a	I _{D(on)}	V _{DS} ≥ - 10 V, V _{GS} = - 10 V	- 30			A
Drain-Source On-State Resistance ^a	R _{DS(on)}	V _{GS} = - 10 V, I _D = - 15 A		0.0039	0.005	Ω
		V _{GS} = - 4.5 V, I _D = - 10 A		0.0062	0.00775	
Forward Transconductance ^a	g _{fs}	V _{DS} = - 10 V, I _D = - 15 A		24		S
Dynamic ^b						
Input Capacitance	C _{iss}	V _{DS} = - 15 V, V _{GS} = 0 V, f = 1 MHz		6000		pF
Output Capacitance	C _{oss}			860		
Reverse Transfer Capacitance	C _{rss}			790		
Total Gate Charge	Q _g	V _{DS} = - 15 V, V _{GS} = - 10 V, I _D = - 20 A		129	195	nC
Gate-Source Charge	Q _{gs}	V _{DS} = - 15 V, V _{GS} = - 4.5 V, I _D = - 20 A		61	95	
Gate-Drain Charge	Q _{gd}			16.5		
				23.5		
Gate Resistance	R _g	f = 1 MHz	0.6	3.0	6.0	Ω
Turn-On Delay Time	t _{d(on)}	V _{DD} = - 15 V, R _L = 1.5 Ω I _D ≡ - 10 A, V _{GEN} = - 10 V, R _g = 1 Ω		16	30	ns
Rise Time	t _r			16	30	
Turn-Off DelayTime	t _{d(off)}			80	150	
Fall Time	t _f			20	40	
Turn-On Delay Time	t _{d(on)}	V _{DD} = - 15 V, R _L = 1.5 Ω I _D ≡ - 10 A, V _{GEN} = - 4.5 V, R _g = 1 Ω		75	150	
Rise Time	t _r			130	260	
Turn-Off DelayTime	t _{d(off)}			60	120	
Fall Time	t _f			40	80	
Drain-Source Body Diode Characteristics						
Continous Source-Drain Diode Current	I _S	T _C = 25 °C			- 29	A
Pulse Diode Forward Current	I _{SM}				- 70	
Body Diode Voltage	V _{SD}	I _S = - 3 A, V _{GS} = 0 V		- 0.71	- 1.2	V
Body Diode Reverse Recovery Time	t _{rr}	I _F = - 5 A, di/dt = 100 A/μs, T _J = 25 °C		67	130	ns
Body Diode Reverse Recovery Charge	Q _{rr}			74	150	nC
Reverse Recovery Fall Time	t _a			22		ns
Reverse Recovery Rise Time	t _b			45		

Notes:

- a. Pulse test; pulse width $\leq 300\text{ }\mu\text{s}$, duty cycle $\leq 2\%$.
b. Guaranteed by design, not subject to production testing.

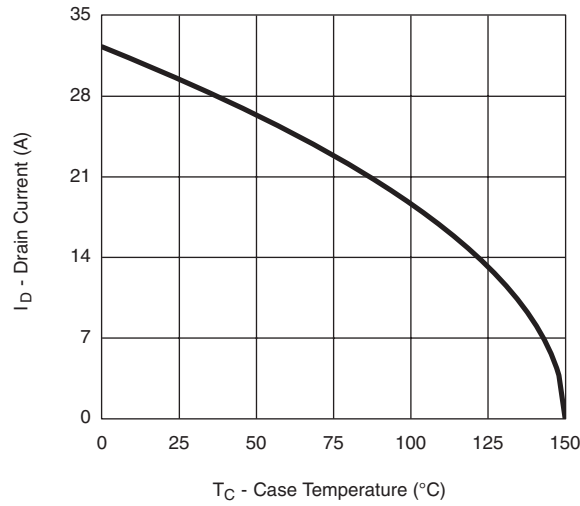
Stresses beyond those listed under "Absolute Maximum Ratings" may cause permanent damage to the device. These are stress ratings only, and functional operation of the device at these or any other conditions beyond those indicated in the operational sections of the specifications is not implied. Exposure to absolute maximum rating conditions for extended periods may affect device reliability.

**TYPICAL CHARACTERISTICS** 25 °C, unless otherwise noted**Output Characteristics****Transfer Characteristics****On-Resistance vs. Drain Current****Capacitance****Gate Charge****On-Resistance vs. Junction Temperature**

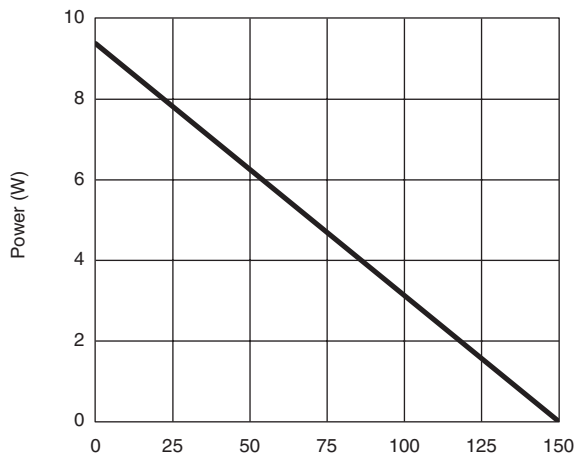
TYPICAL CHARACTERISTICS 25 °C, unless otherwise noted**Source-Drain Diode Forward Voltage****On-Resistance vs. Gate-to-Source Voltage****Threshold Voltage****Single Pulse Power, Junction-to-Ambient*** $V_{GS} >$ minimum V_{GS} at which $R_{DS(on)}$ is specified**Safe Operating Area**



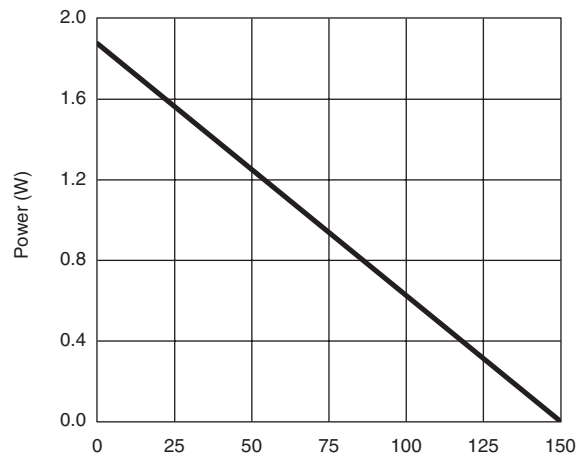
MOSFET TYPICAL CHARACTERISTICS 25 °C, unless otherwise noted



Current Derating*

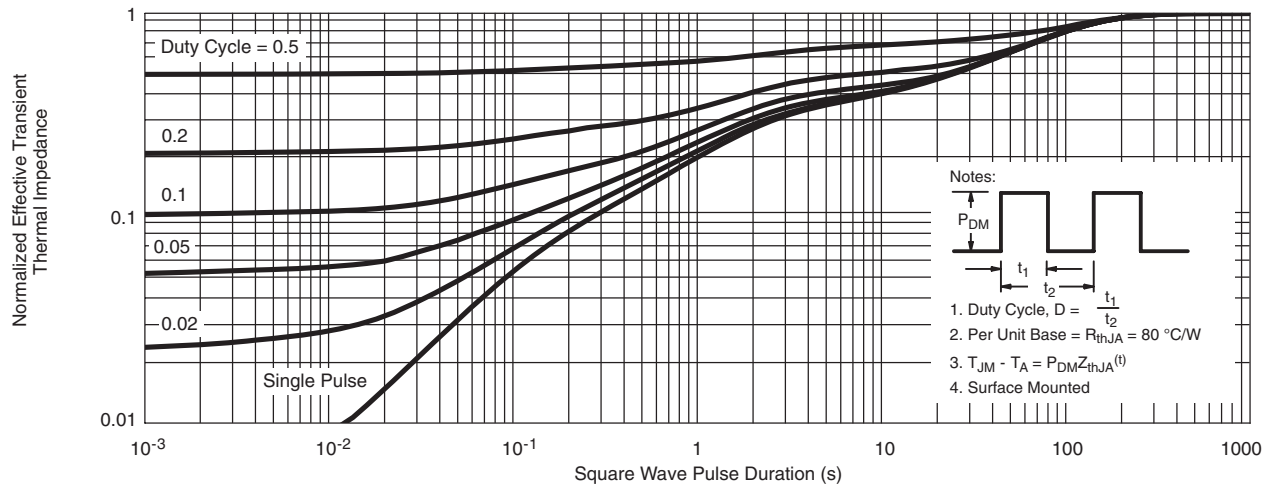
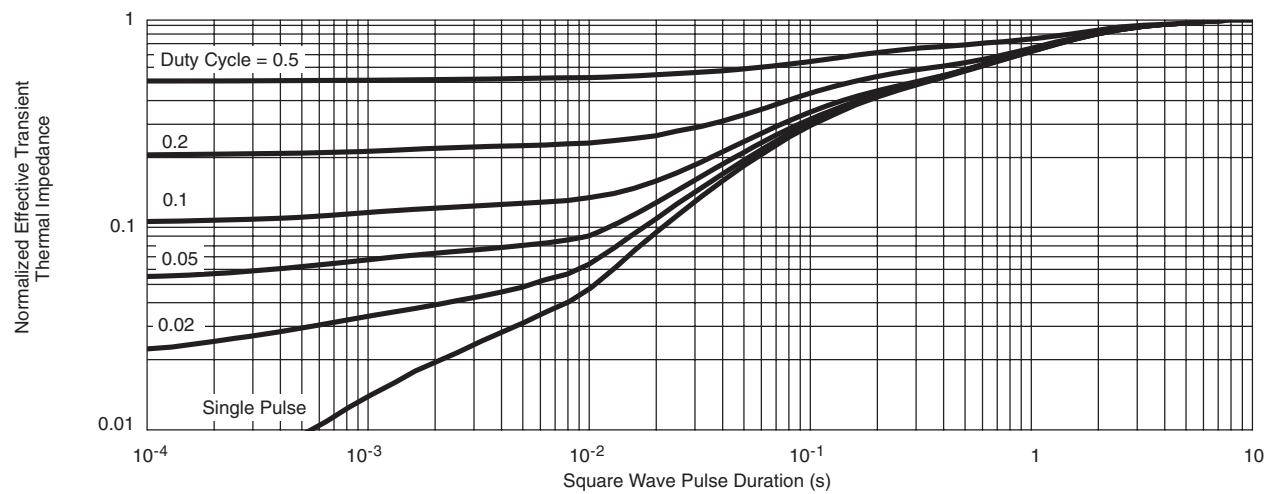


Power, Junction-to-Foot



Power Derating, Junction-to-Ambient

* The power dissipation P_D is based on $T_{J(max)} = 175$ °C, using junction-to-case thermal resistance, and is more useful in settling the upper dissipation limit for cases where additional heatsinking is used. It is used to determine the current rating, when this rating falls below the package limit.

TYPICAL CHARACTERISTICS 25 °C, unless otherwise noted**Normalized Thermal Transient Impedance, Junction-to-Ambient****Normalized Thermal Transient Impedance, Junction-to-Foot**

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